

Epi - Wafer

n-Type GaN



Feature n-Type GaN Epi. Wafer
Single side polished (Growth surface)

Diameter 2" (50.8mm)

Thickness (Included substrate) ~ 4 μ m (+/-10% std)

Structure n-GaN / u-GaN / Sapphire substrate



GaN on Sapphire Wafer

Characteristics (at 25°C)

| Parameter | | Typ. | Test Conditions |
|-----------------|-----------------------|---|-------------------------------|
| PL measurement | Peak wavelength | 362nm \pm 2nm | Etamax PLATO Laser : 266nm |
| | Uniformity STD | <3% | |
| | FWHM | <10nm | |
| | FWHM STD | <3% | |
| Thickness | Thickness | ~ 4 μ m (+/-10% std) | |
| | Thickness STD | <10% | |
| XRD | (002) | <400 arcsec | Panalytical HRXRD |
| | (102) | <500 arcsec | |
| Hall | Carrier Concentration | $\geq -1 \times 10^{18}$ /cm ³ | Accent HL5500 |
| | Mobility | ≤ 200 cm ² /V-sec | |
| Doping material | Si | used | - |
| | Mg | N/A | |

Normalized Single Spectrum(300 ~ 700nm)

